# 74HC1G08-Q100; 74HCT1G08-Q100

# 2-input AND gate Rev. 2 — 16 August 2012

**Product data sheet** 

#### **General description** 1.

74HC1G08-Q100 and 74HCT1G08-Q100 are high-speed, Si-gate CMOS devices. They provide a 2-input AND function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half of those of the 74HC08-Q100 and 74HCT08-Q100.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

#### **Features and benefits** 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

#### **Ordering information** 3.

Table 1. **Ordering information** 

| Type number      | Package           |        |   |          |  |  |  |  |
|------------------|-------------------|--------|---|----------|--|--|--|--|
|                  | Temperature range | Name   | Description   | Version  |  |  |  |  |
| 74HC1G08GW-Q100  | –40 °C to +125 °C | TSSOP5 | plastic thin shrink small outline package; 5 leads; | SOT353-1 |  |  |  |  |
| 74HCT1G08GW-Q100 |                   |        | body width 1.25 mm                                  |          |  |  |  |  |
| 74HC1G08GV-Q100  | –40 °C to +125 °C | SC-74A | plastic surface-mounted package; 5 leads            | SOT753   |  |  |  |  |
| 74HCT1G08GV-Q100 | _                 |        |   |          |  |  |  |  |



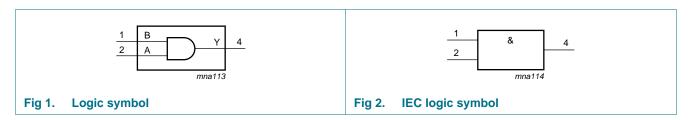
# 4. Marking

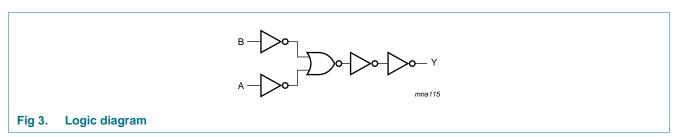
#### Table 2. Marking codes

| Type number      | Marking <sup>[1]</sup> |
|------------------|------------------------|
| 74HC1G08GW-Q100  | HE                     |
| 74HCT1G08GW-Q100 | TE                     |
| 74HC1G08GV-Q100  | H08                    |
| 74HCT1G08GV-Q100 | T08                    |

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

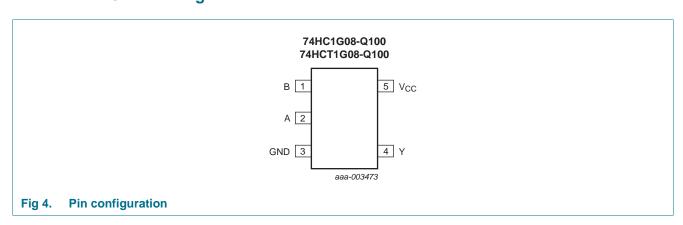
# 5. Functional diagram





# 6. Pinning information

### 6.1 Pinning



# 6.2 Pin description

Table 3. Pin description

| Symbol          | Pin | Description    |
|-----------------|-----|----------------|
| В               | 1   | data input     |
| Α               | 2   | data input     |
| GND             | 3   | ground (0 V)   |
| Υ               | 4   | data output    |
| V <sub>CC</sub> | 5   | supply voltage |

# 7. Functional description

#### Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

| Input |   | Output |
|-------|---|--------|
| Α     | В | Υ      |
| L     | L | L      |
| L     | Н | L      |
| Н     | L | L      |
| Н     | Н | Н      |

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

| Symbol           | Parameter               | Conditions  | Min   | Max   | Unit |
|------------------|-------------------------|---|-------|-------|------|
| $V_{CC}$         | supply voltage          |   | -0.5  | +7.0  | V    |
| I <sub>IK</sub>  | input clamping current  | $V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$                       | -     | ±20   | mA   |
| I <sub>OK</sub>  | output clamping current | $V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$                       | -     | ±20   | mA   |
| Io               | output current          | $-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$ | -     | ±12.5 | mA   |
| I <sub>CC</sub>  | supply current          |   | -     | 25    | mA   |
| $I_{GND}$        | ground current          |   | -25   | -     | mA   |
| T <sub>stg</sub> | storage temperature     |   | -65   | +150  | °C   |
| P <sub>tot</sub> | total power dissipation | $T_{amb}$ = -40 °C to +125 °C   | [2] - | 200   | mW   |
|                  |                         |   |       |       |      |

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>[2]</sup> Above 55  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.

# 9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

| Symbol                | Parameter             | Conditions               | 74HC10 | 308-Q100 | )        | 74HCT1 | 00  | Unit     |      |
|-----------------------|-----------------------|--------------------------|--------|----------|----------|--------|-----|----------|------|
|                       |                       |                          | Min    | Тур      | Max      | Min    | Тур | Max      |      |
| $V_{CC}$              | supply voltage        |                          | 2.0    | 5.0      | 6.0      | 4.5    | 5.0 | 5.5      | V    |
| VI                    | input voltage         |                          | 0      | -        | $V_{CC}$ | 0      | -   | $V_{CC}$ | V    |
| Vo                    | output voltage        |                          | 0      | -        | $V_{CC}$ | 0      | -   | $V_{CC}$ | V    |
| T <sub>amb</sub>      | ambient temperature   |                          | -40    | +25      | +125     | -40    | +25 | +125     | °C   |
| $\Delta t / \Delta V$ | input transition rise | $V_{CC} = 2.0 \text{ V}$ | -      | -        | 625      | -      | -   | -        | ns/V |
|                       | and fall rate         | $V_{CC} = 4.5 \text{ V}$ | -      | -        | 139      | -      | -   | 139      | ns/V |
|                       |                       | $V_{CC} = 6.0 \text{ V}$ | -      | -        | 83       | -      | -   | -        | ns/V |

# 10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T<sub>amb</sub> = 25 °C.

| Symbol          | Parameter               | Conditions   | -40  | °C to + | 85 °C | –40 °C | Unit |    |
|-----------------|-------------------------|--|------|---------|-------|--------|------|----|
|                 |                         |  |      | Тур     | Max   | Min    | Max  |    |
| 74HC1G0         | 8-Q100                  |  | '    | '       | '     | '      | '    | •  |
| $V_{IH}$        | HIGH-level input        | V <sub>CC</sub> = 2.0 V                                      | 1.5  | 1.2     | -     | 1.5    | -    | V  |
| voltage         | voltage                 | V <sub>CC</sub> = 4.5 V                                      | 3.15 | 2.4     | -     | 3.15   | -    | V  |
|                 |                         | $V_{CC} = 6.0 \text{ V}$                                     | 4.2  | 3.2     | -     | 4.2    | -    | V  |
| $V_{IL}$        | LOW-level input         | V <sub>CC</sub> = 2.0 V                                      | -    | 8.0     | 0.5   | -      | 0.5  | V  |
| voltage         | V <sub>CC</sub> = 4.5 V | -  | 2.1  | 1.35    | -     | 1.35   | V    |    |
|                 |                         | $V_{CC} = 6.0 \text{ V}$                                     | -    | 2.8     | 1.8   | -      | 1.8  | V  |
| $V_{OH}$        | HIGH-level output       | $V_I = V_{IH}$ or $V_{IL}$                                   |      |         |       |        |      |    |
|                 | voltage                 | $I_O = -20 \mu A; V_{CC} = 2.0 V$                            | 1.9  | 2.0     | -     | 1.9    | -    | V  |
|                 |                         | $I_O = -20 \mu A; V_{CC} = 4.5 V$                            | 4.4  | 4.5     | -     | 4.4    | -    | V  |
|                 |                         | $I_O = -20 \mu A; V_{CC} = 6.0 V$                            | 5.9  | 6.0     | -     | 5.9    | -    | V  |
|                 |                         | $I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$            | 4.13 | 4.32    | -     | 3.7    | -    | V  |
|                 |                         | $I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$            | 5.63 | 5.81    | -     | 5.2    | -    | V  |
| $V_{OL}$        | LOW-level output        | $V_I = V_{IH}$ or $V_{IL}$                                   |      |         |       |        |      |    |
|                 | voltage                 | $I_O = 20 \mu A; V_{CC} = 2.0 V$                             | -    | 0       | 0.1   | -      | 0.1  | V  |
|                 |                         | $I_O = 20 \mu A; V_{CC} = 4.5 V$                             | -    | 0       | 0.1   | -      | 0.1  | V  |
|                 |                         | $I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$                     | -    | 0       | 0.1   | -      | 0.1  | V  |
|                 |                         | $I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$               | -    | 0.15    | 0.33  | -      | 0.4  | V  |
|                 |                         | $I_{O} = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$             | -    | 0.16    | 0.33  | -      | 0.4  | V  |
| I <sub>I</sub>  | input leakage current   | $V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$              | -    | -       | 1.0   | -      | 1.0  | μΑ |
| I <sub>CC</sub> | supply current          | $V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$ | -    | -       | 10    | -      | 20   | μΑ |
| Cı              | input capacitance       |  | -    | 1.5     | -     | -      | -    | pF |

 Table 7.
 Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb}$  = 25 °C.

| Symbol           | Parameter                 | Conditions   | -40  | °C to + | 85 °C | –40 °C | Unit |    |
|------------------|---------------------------|--|------|---------|-------|--------|------|----|
|                  |                           |  | Min  | Тур     | Max   | Min    | Max  |    |
| 74HCT1G          | 08-Q100                   |  |      |         |       |        |      |    |
| V <sub>IH</sub>  | HIGH-level input voltage  | $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$   | 2.0  | 1.6     | -     | 2.0    | -    | V  |
| V <sub>IL</sub>  | LOW-level input voltage   | $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$   | -    | 1.2     | 8.0   | -      | 0.8  | V  |
| V <sub>OH</sub>  | HIGH-level output         | $V_I = V_{IH}$ or $V_{IL}$   |      |         |       |        |      |    |
|                  | voltage                   | $I_O = -20 \mu A; V_{CC} = 4.5 V$  | 4.4  | 4.5     | -     | 4.4    | -    | V  |
|                  |                           | $I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$  | 4.13 | 4.32    | -     | 3.7    | -    | V  |
| $V_{OL}$         | LOW-level output          | $V_I = V_{IH}$ or $V_{IL}$   |      |         |       |        |      |    |
|                  | voltage                   | $I_O = 20 \mu A; V_{CC} = 4.5 V$   | -    | 0       | 0.1   | -      | 0.1  | V  |
|                  |                           | $I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$   | -    | 0.15    | 0.33  | -      | 0.4  | V  |
| l <sub>l</sub>   | input leakage current     | $V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$  | -    | -       | 1.0   | -      | 1.0  | μΑ |
| I <sub>CC</sub>  | supply current            | $V_1 = V_{CC}$ or GND; $I_0 = 0$ A;<br>$V_{CC} = 5.5 \text{ V}$  | -    | -       | 10    | -      | 20   | μΑ |
| Δl <sub>CC</sub> | additional supply current | per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_I = V_{CC} - 2.1 \text{ V};$ $I_O = 0 \text{ A}$ | -    | -       | 500   | -      | 850  | μΑ |
| Cı               | input capacitance         |  | -    | 1.5     | -     | -      | -    | рF |

# 11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V;  $t_r = t_f \le 6.0$  ns; All typical values are measured at  $T_{amb} = 25$  °C. For test circuit see <u>Figure 6</u>

| Symbol          | Parameter                     | Conditions                                    |            | -40 | °C to +8 | 35 °C | -40 °C | to +125 °C | Unit |
|-----------------|-------------------------------|---|------------|-----|----------|-------|--------|------------|------|
|                 |                               |   |            | Min | Тур      | Max   | Min    | Max        |      |
| 74HC1G          | 08-Q100                       |   |            |     | '        | '     | '      |            |      |
| t <sub>pd</sub> | propagation delay             | A and B to Y; see Figure 5                    | <u>[1]</u> |     |          |       |        |            |      |
|                 |                               | $V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$ |            | -   | 25       | 115   | -      | 135        | ns   |
|                 |                               | $V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$ |            | -   | 9        | 23    | -      | 27         | ns   |
|                 |                               | $V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$ |            | -   | 7        | -     | -      | -          | ns   |
|                 |                               | $V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$ |            | -   | 8        | 20    | -      | 23         | ns   |
| C <sub>PD</sub> | power dissipation capacitance | $V_I = GND \text{ to } V_{CC}$                | [2]        | -   | 19       | -     | -      | -          | pF   |
| 74HCT10         | G08-Q100                      |   |            |     |          |       |        |            |      |
| t <sub>pd</sub> | propagation delay             | A and B to Y; see Figure 5                    | <u>[1]</u> |     |          |       |        |            |      |
|                 |                               | $V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$ |            | -   | 11       | 23    | -      | 27         | ns   |
|                 |                               | $V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$ |            | -   | 11       | -     | -      | -          | ns   |

 Table 8.
 Dynamic characteristics ...continued

GND = 0 V;  $t_r = t_f \le 6.0$  ns; All typical values are measured at  $T_{amb} = 25$  °C. For test circuit see Figure 6

| Symbol   | Parameter                     | Conditions                      |     | -40 °C to +85 °C |     | Unit |     |     |    |
|----------|-------------------------------|---------------------------------|-----|------------------|-----|------|-----|-----|----|
|          |                               |                                 |     | Min              | Тур | Max  | Min | Max |    |
| $C_{PD}$ | power dissipation capacitance | $V_I = GND$ to $V_{CC} - 1.5 V$ | [2] | -                | 21  | -    | -   | -   | pF |

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $\,$   $\,$   $\,$   $\,$   $\,$   $\,$   $\,$   $\,$  C<sub>PD</sub> is used to determine the dynamic power dissipation P<sub>D</sub> ( $\mu$ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

f<sub>i</sub> = input frequency in MHz

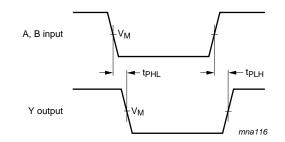
f<sub>o</sub> = output frequency in MHz

C<sub>L</sub> = output load capacitance in pF

V<sub>CC</sub> = supply voltage in Volts

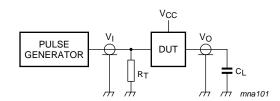
 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$ 

## 12. Waveforms



For 74HC1G08-Q100:  $V_M = 0.5 \times V_{CC}$ ;  $V_I = GND$  to  $V_{CC}$ For 74HCT1G08-Q100:  $V_M = 1.3$  V;  $V_I = GND$  to 3.0 V





Test data is given in Table 8. Definitions for test circuit:

 $\ensuremath{C_L}$  = Load capacitance including jig and probe capacitance

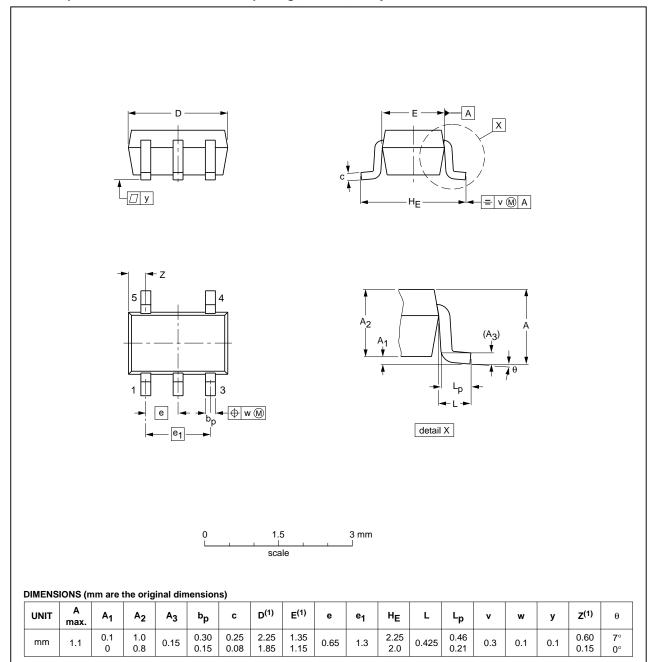
 $R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator

Fig 6. Test circuit for measuring switching times

# 13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

| OUTLINE  |     | REFER  | ENCES  | EUROPEAN   | ISSUE DATE                       |
|----------|-----|--------|--------|------------|----------------------------------|
| VERSION  | IEC | JEDEC  | JEITA  | PROJECTION | 1330E DATE                       |
| SOT353-1 |     | MO-203 | SC-88A |            | <del>-00-09-01</del><br>03-02-19 |

Fig 7. Package outline SOT353-1 (TSSOP5)

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#### Plastic surface-mounted package; 5 leads

**SOT753** 

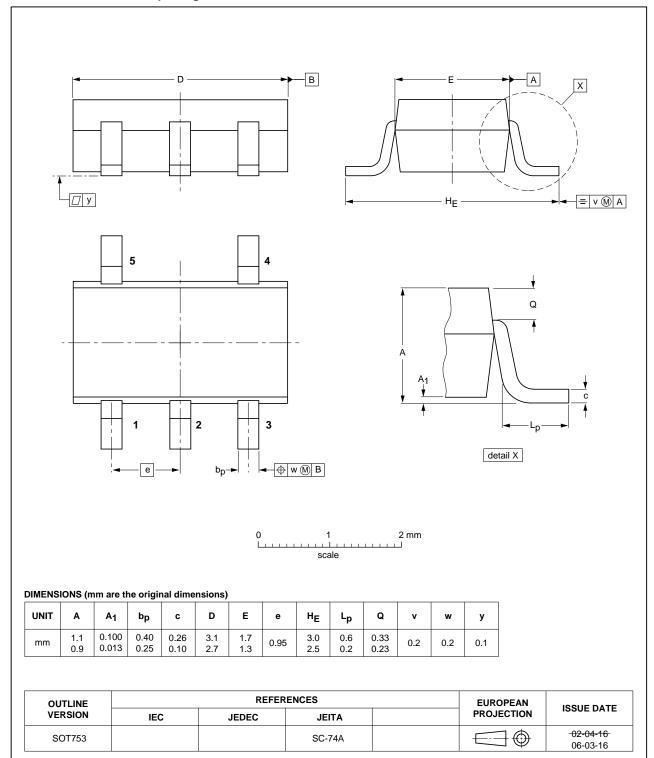


Fig 8. Package outline SOT753 (SC-74A)

74HC\_HCT1G08\_Q100

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# 14. Abbreviations

#### Table 9. Abbreviations

| Acronym | Description                             |
|---------|---|
| CMOS    | Complementary Metal Oxide Semiconductor |
| TTL     | Transistor-Transistor Logic             |
| HBM     | Human Body Model                        |
| ESD     | ElectroStatic Discharge                 |
| MM      | Machine Model                           |
| DUT     | Device Under Test                       |

# 15. Revision history

### Table 10. Revision history

| Document ID           | Release<br>date              | Data sheet status            | Change notice | Supersedes            |
|-----------------------|------------------------------|------------------------------|---------------|-----------------------|
| 74HC_HCT1G08_Q100 v.2 | 20120816                     | Product data sheet           | -             | 74HC_HCT1G08_Q100 v.1 |
| Modifications:        | <ul> <li>Added pi</li> </ul> | in 1 location note (Table 2) |               |                       |
| 74HC_HCT1G08_Q100 v.1 | 20120605                     | Product data sheet           | -             | -                     |

# 16. Legal information

#### 16.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# 74HC1G08-Q100; 74HCT1G08-Q100

2-input AND gate

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# 74HC1G08-Q100; 74HCT1G08-Q100

2-input AND gate

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